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MOSFET - Power, N-Channel, SUPERFET III, FRFET 650 V, 40 A, 82 mΩ



NTP082N65S3HF

Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

Features

- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 70 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 81 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(\text{eff.})} = 722 \text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

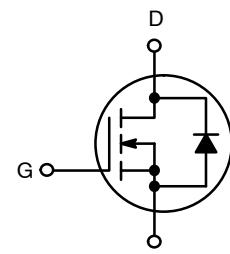
Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies
- EV Charger
- UPS / Solar

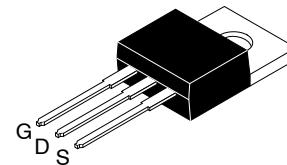
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V_{DSS}	$R_{DS(\text{ON}) \text{ MAX}}$	$I_D \text{ MAX}$
650 V	82 mΩ @ 10 V	40 A

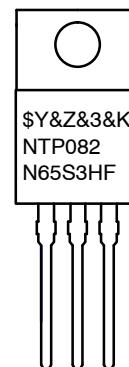


POWER MOSFET



**TO-220
CASE 340AT**

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &3 = Data Code (Year & Week)
 &K = Lot
 NTP082N65S3HF = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTP082N65S3HF

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain to Source Voltage		650	V
V _{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I _D	Drain Current	– Continuous (T _C = 25°C)	40	A
		– Continuous (T _C = 100°C)	25.5	
I _{DM}	Drain Current	– Pulsed (Note 1)	100	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		510	mJ
I _{AS}	Avalanche Current (Note 2)		4.8	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		3.13	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P _D	Power Dissipation	(T _C = 25°C)	313	W
		– Derate Above 25°C	2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 4.8 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 20 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTP082N65S3HF	NTP082N65S3HF	TO-220	Tube	N/A	N/A	50 Units

NTP082N65S3HF

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 25^\circ\text{C}$	650			V
		$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}, T_J = 150^\circ\text{C}$	700			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10 \text{ mA}$, Referenced to 25°C		0.7		$^\circ\text{C}$
Id _{SS}	Zero Gate Voltage Drain Current	$V_{DS} = 650 \text{ V}, V_{GS} = 0 \text{ V}$		10		μA
		$V_{DS} = 520 \text{ V}, T_C = 125^\circ\text{C}$		124		
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			± 100	nA

ON CHARACTERISTICS

$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 4 \text{ mA}$	3.0		5.0	V
$R_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		70	82	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$		24		S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		3410		pF
C_{oss}	Output Capacitance			70		pF
$C_{oss(\text{eff.})}$	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$		722		pF
$C_{oss(\text{er.})}$	Energy Related Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$		126		pF
$Q_{g(\text{tot})}$	Total Gate Charge at 10 V	$V_{DS} = 400 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$ (Note 4)		81		nC
Q_{gs}	Gate to Source Gate Charge			24		nC
Q_{gd}	Gate to Drain "Miller" Charge			32		nC
ESR	Equivalent Series Resistance	$f = 1 \text{ MHz}$		1.9		Ω

SWITCHING CHARACTERISTICS

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 400 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$ $R_g = 3 \Omega$ (Note 4)		26		ns
t_r	Turn-On Rise Time			21		ns
$t_{d(\text{off})}$	Turn-Off Delay Time			80		ns
t_f	Turn-Off Fall Time			4.0		ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I_S	Maximum Continuous Source to Drain Diode Forward Current			40		A
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current			100		A
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{SD} = 20 \text{ A}$			1.3	V
t_{rr}	Reverse Recovery Time	$V_{DD} = 400 \text{ V}, I_{SD} = 20 \text{ A},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$		108		ns
Q_{rr}	Reverse Recovery Charge			410		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

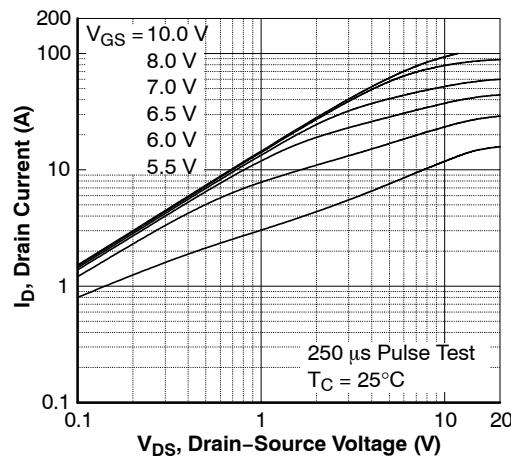


Figure 1. On-Region Characteristics

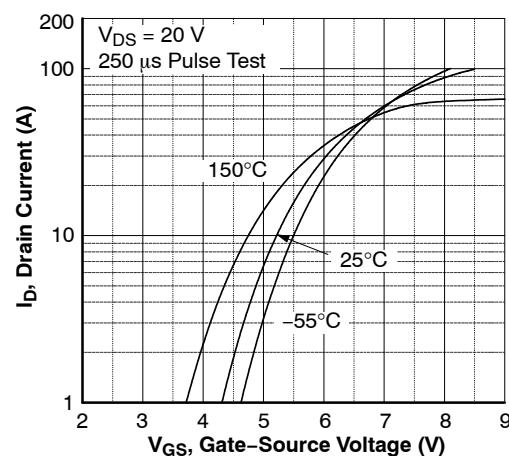


Figure 2. Transfer Characteristics

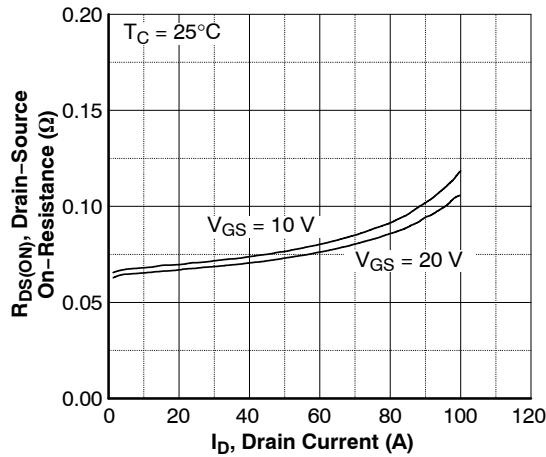


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

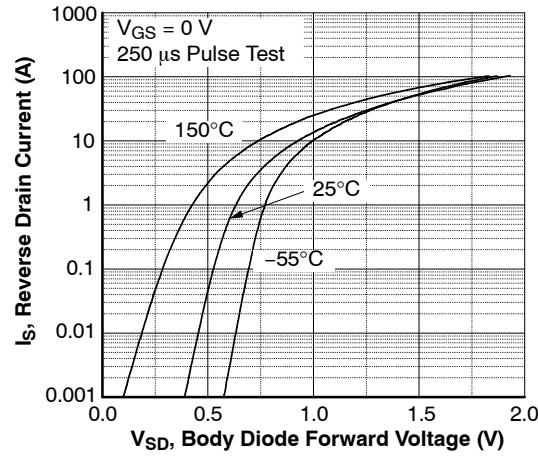


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

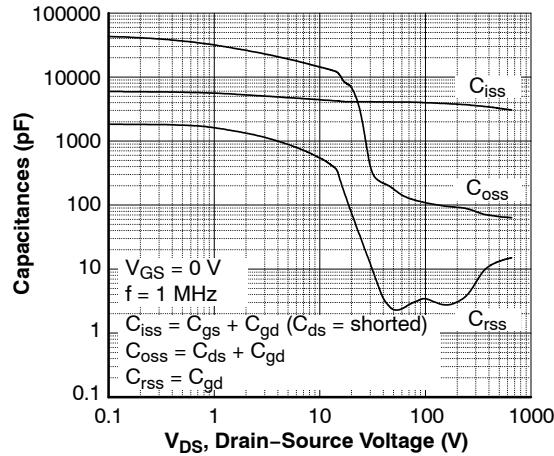


Figure 5. Capacitance Characteristics

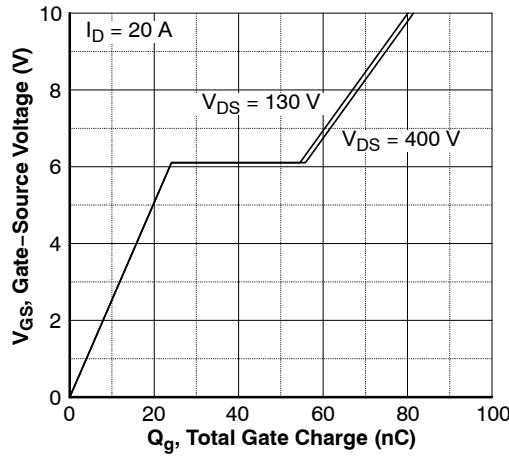


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

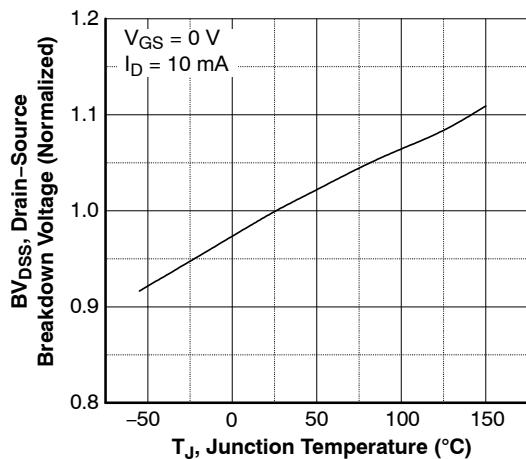


Figure 7. Breakdown Voltage Variation
vs. Temperature

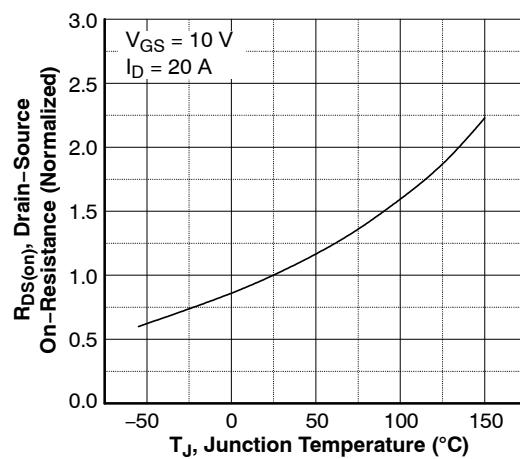


Figure 8. On-Resistance Variation
vs. Temperature

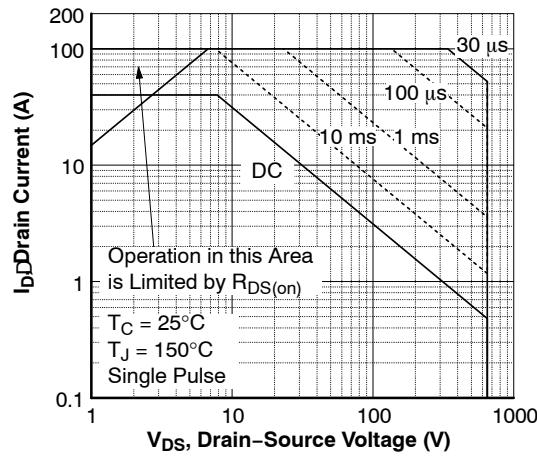


Figure 9. Maximum Safe Operating Area

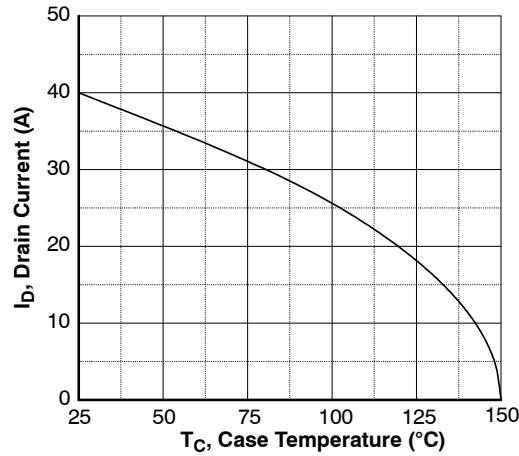


Figure 10. Maximum Drain Current
vs. Case Temperature

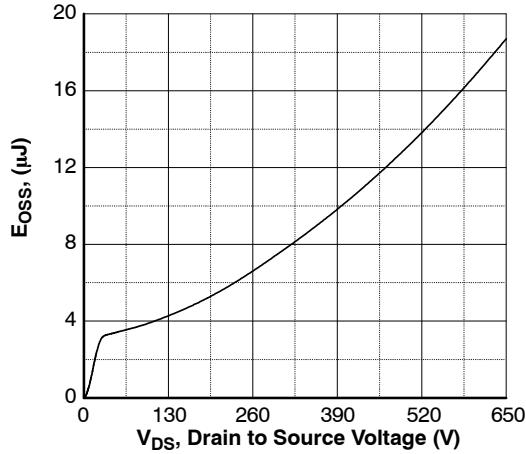


Figure 11. E_OSS vs. Drain to Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

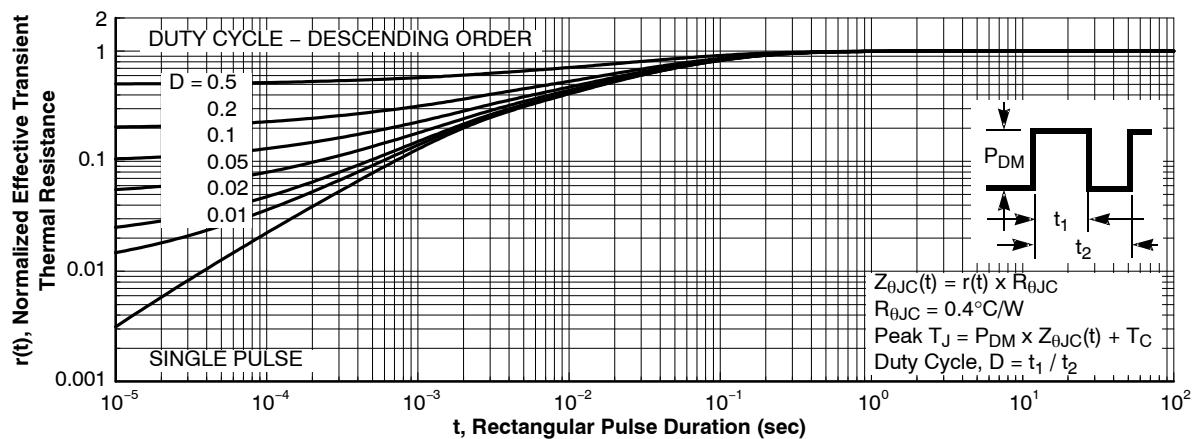


Figure 12. Transient Thermal Response Curve

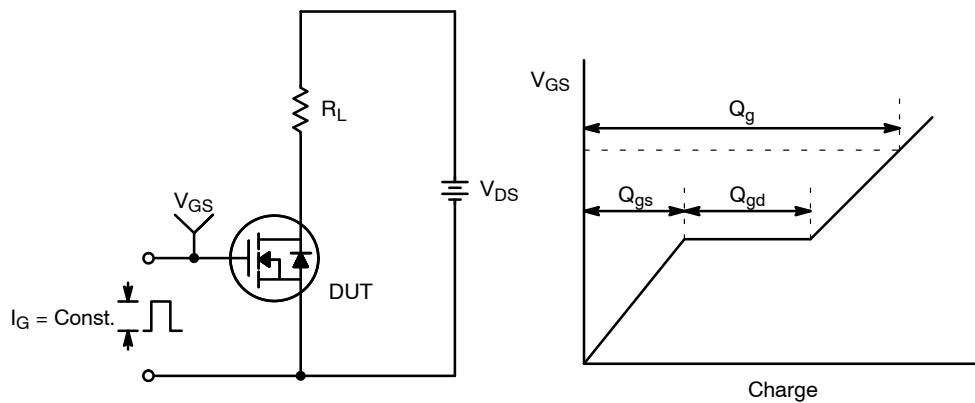


Figure 13. Gate Charge Test Circuit & Waveform

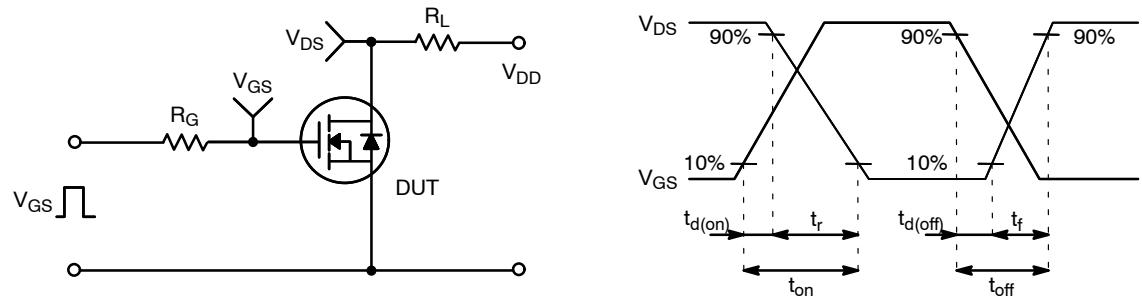


Figure 14. Resistive Switching Test Circuit & Waveforms

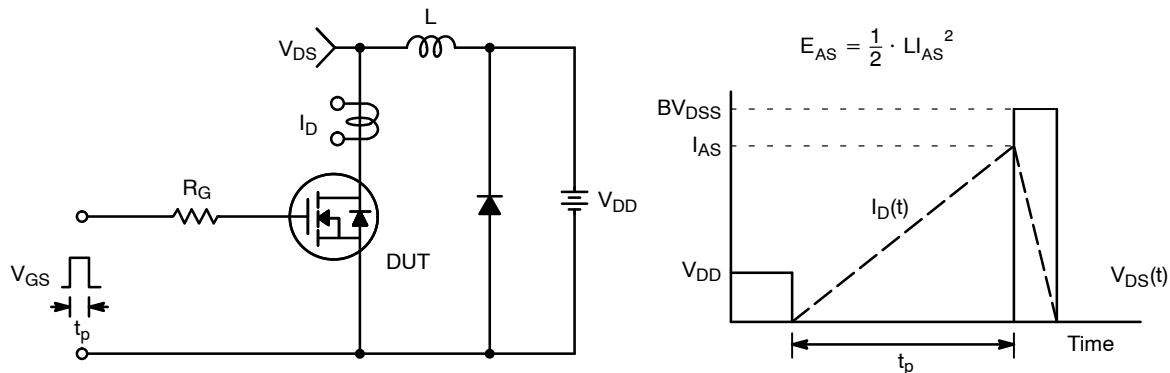


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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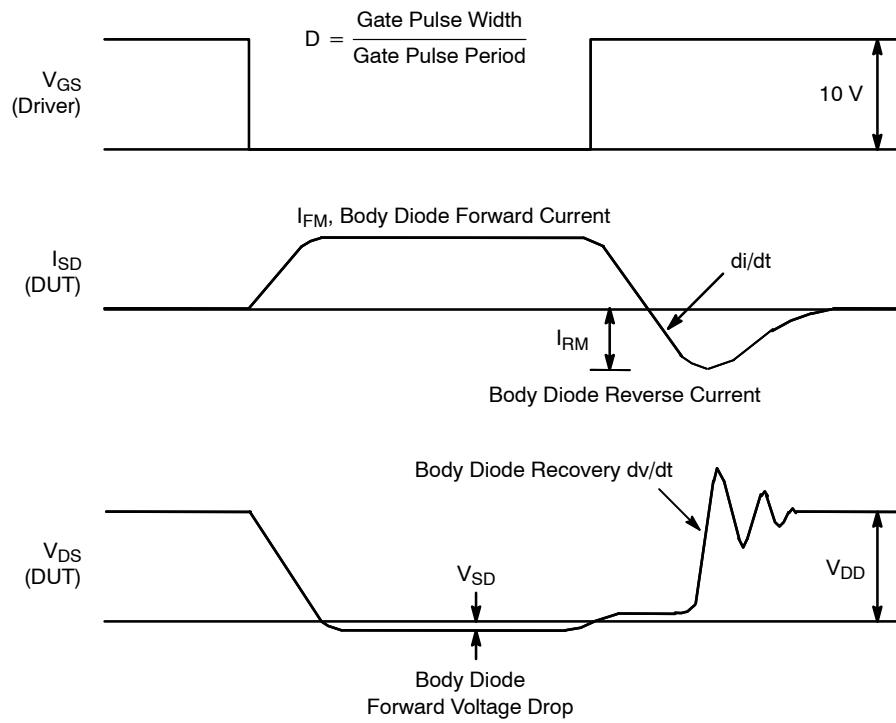
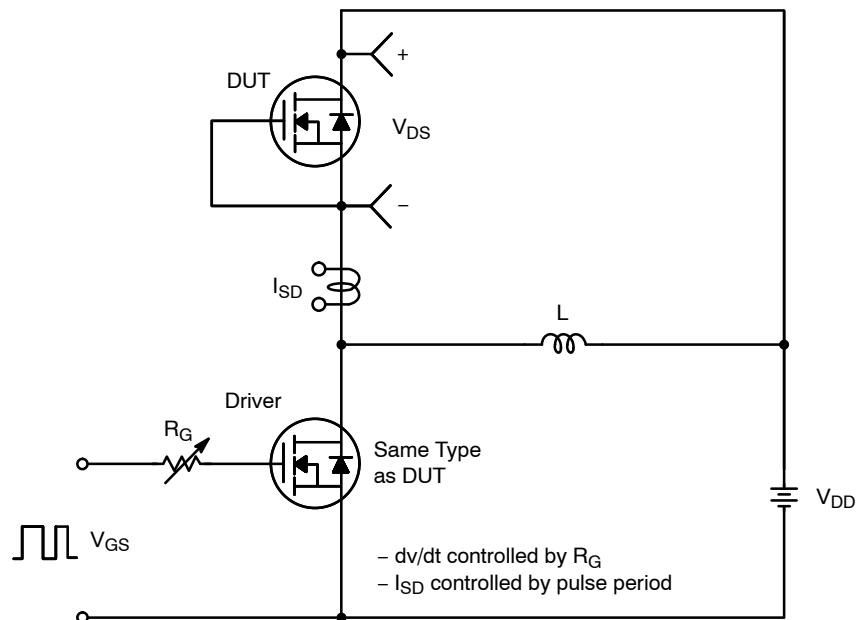
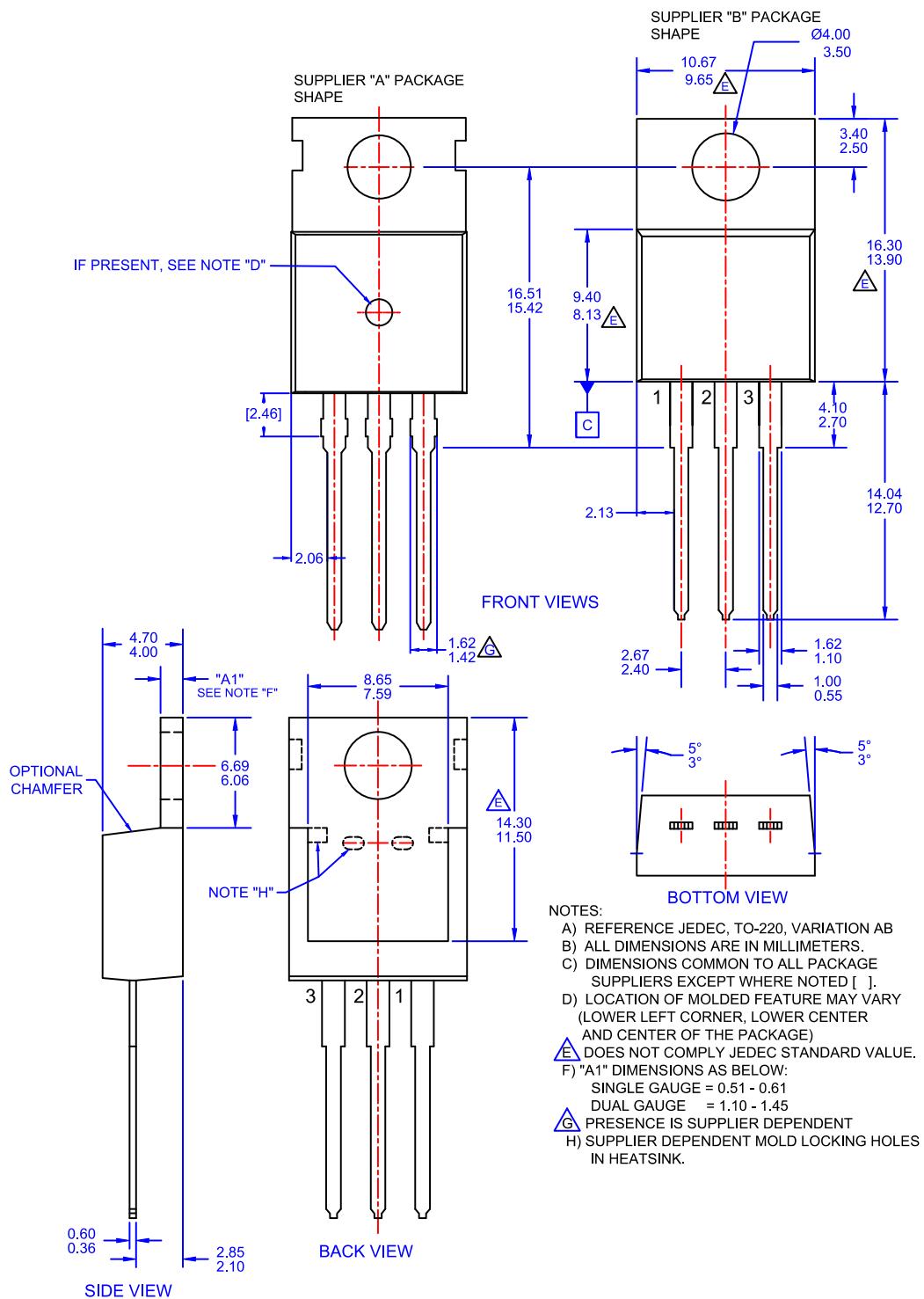


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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CASE 340AT
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